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Kind regards,

Team Nexperia



PMST3906

40 V, 200 mA PNP switching transistor Rev. 05 — 29 April 2009

Product data sheet

Product profile

1.1 General description

PNP switching transistor in a SOT323 (SC-70) very small Surface-Mounted Device (SMD) plastic package.

NPN complement: PMST3904.

1.2 Features

Collector current: I_C ≤ -200 mA

Collector-emitter voltage: V_{CEO} ≤ -40 V

Very small SMD plastic package

1.3 Applications

General amplification and switching

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
Ic	collector current		-	-	-200	mA

Pinning information

Table 2. **Pinning**

	- I IIIIIII		
Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	3	3
3	collector		1—
		1	' \
		1 📙 🗀 2	2
			sym013



40 V, 200 mA PNP switching transistor

3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PMST3906	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMST3906	*2A

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-200	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I_{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	625	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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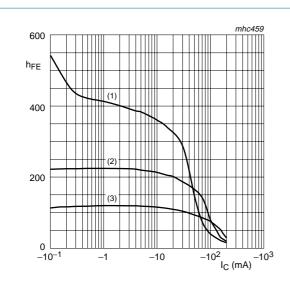
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = -30 \text{ V}$	-	-	-50	nA
I _{EBO}	emitter-base cut-off current	$I_C = 0 A; V_{EB} = -6 V$	-	-	-50	nA
h _{FE}	DC current gain	$V_{CE} = -1 V$				
		$I_{C} = -0.1 \text{ mA}$	60	-	-	
		$I_C = -1 \text{ mA}$	80	-	-	
		$I_C = -10 \text{ mA}$	100	-	300	
		$I_C = -50 \text{ mA}$	60	-	-	
		$I_C = -100 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-	-250	mV
	saturation voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-400	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-950	mV
t _d	delay time	$I_C = -10 \text{ mA};$ $I_{Bon} = -1 \text{ mA};$ $I_{Boff} = 1 \text{ mA}$	-	-	35	ns
t _r	rise time		-	-	35	ns
t _{on}	turn-on time	Boff - TIIIA	-	-	70	ns
t _s	storage time		-	-	225	ns
t _f	fall time		-	-	75	ns
t _{off}	turn-off time		-	-	300	ns
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -5 \text{ V};$ f = 1 MHz	-	-	4.5	pF
C _e	emitter capacitance	$I_C = I_c = 0 \text{ A};$ $V_{EB} = -500 \text{ mV};$ f = 1 MHz	-	-	10	pF
f _T	transition frequency	$I_C = -10 \text{ mA};$ $V_{CE} = -20 \text{ V};$ f = 100 MHz	250	-	-	MHz
NF	noise figure	$I_{C} = -100 \ \mu A;$ $V_{CE} = -5 \ V; \ R_{S} = 1 \ k\Omega;$ $f = 10 \ Hz \ to \ 15.7 \ kHz$	-	-	4	dB

40 V, 200 mA PNP switching transistor



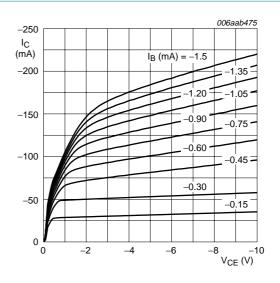
$$V_{CE} = -1 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

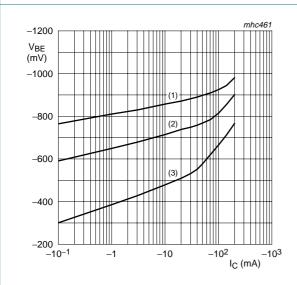
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 2. Collector current as a function of collector-emitter voltage; typical values



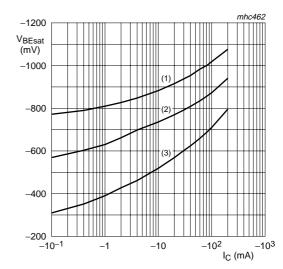


(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 3. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$

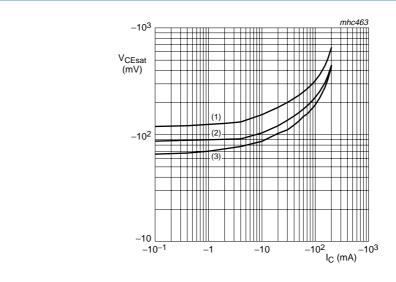
(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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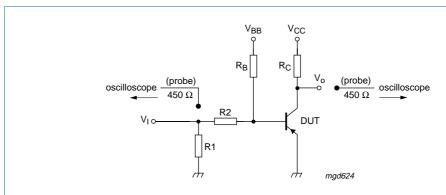


$$I_{\rm C}/I_{\rm B} = 10$$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55$ °C

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

8. Test information



 V_{I} = 5 V; t = 500 μs ; t_{p} = 10 μs ; t_{r} = t_{f} \leq 3 ns

R1 = 56 Ω ; R2 = 2.5 k Ω ; R_B = 3.9 k Ω ; R_C = 270 Ω

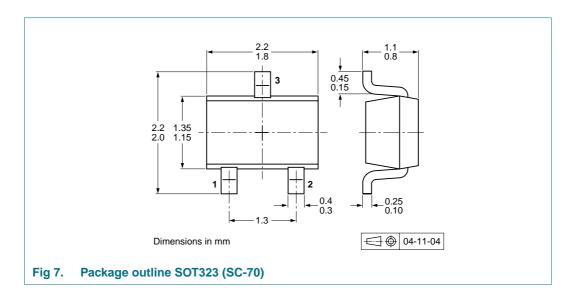
 $V_{BB} = 1.9 \text{ V}; V_{CC} = -3 \text{ V}$

Oscilloscope: input impedance Z_I = 50 Ω

Fig 6. Test circuit for switching times

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9. Package outline



10. Packing information

Table 8. Packing methods

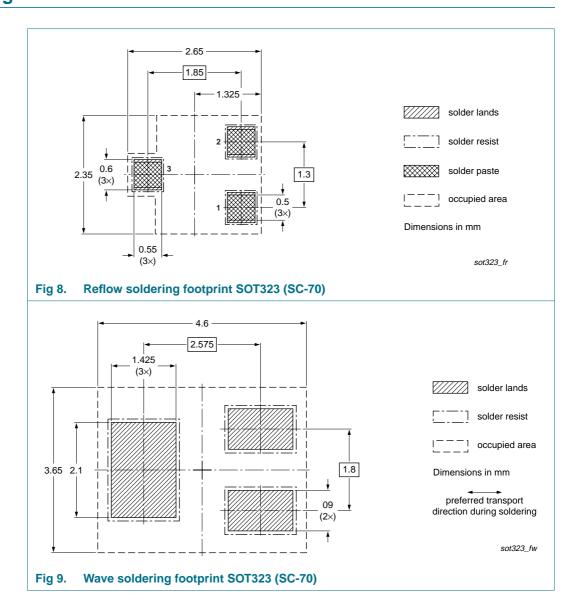
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
PMST3906	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135	

^[1] For further information and the availability of packing methods, see Section 14.

40 V, 200 mA PNP switching transistor

11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMST3906_5	20090429	Product data sheet	-	PMST3906_4		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	• Figure 2: updated					
	 Figure 5: figure notes order amended 					
	Section 10 "Packing information" added					
	Section 11 "Soldering": added					
	 Section 13 "L 	egal information": updated				
PMST3906_4	20040121	Product specification	-	PMST3906_3		
PMST3906_3	19990422	Product specification	-	PMST3906_CNV_2		
PMST3906_CNV_2	19970527	Product specification	-	-		

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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